

NOT RECOMMENDED FOR NEW DESIGN CONTACT US



AP3512E

18V, 2A SYNCHRONOUS DC-DC BUCK CONVERTER

Description

The AP3512E is a 500kHz fixed frequency, current mode, PWM synchronous buck (step-down) DC-DC converter, capable of driving a 2A load with high efficiency, excellent line and load regulation. The AP3512E exhibits high efficiency at light load. The device integrates N-channel power MOSFET switch with low on-resistance. Current mode control provides fast transient response and cycle-by-cycle current limit.

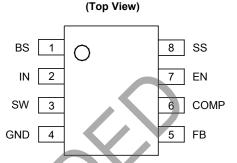
The AP3512E employs complete protection to ensure system security, including output Over Voltage Protection, input Under Voltage Lock Out, programmable Soft-start, Over Temperature Protection and hiccup mode Short Circuit Protection.

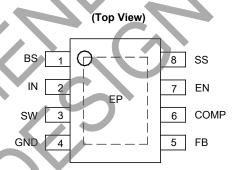
This IC is available in SO-8 and SO-8EP packages.

Features

- Input Voltage Range: 4.5V to 18V
- Fixed 500kHz Frequency
- High Efficiency at Light Load
- Output Current: 2A
- Current Mode Control
- Built-In Over Current Protection
- Built-In Thermal Shutdown Function
- Built-In UVLO Function
- Built-In Over Voltage Protection
- Programmable Soft-Start
- Hiccup Mode SCP
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Pin Assignments





SO-8

SO-8EP

Applications

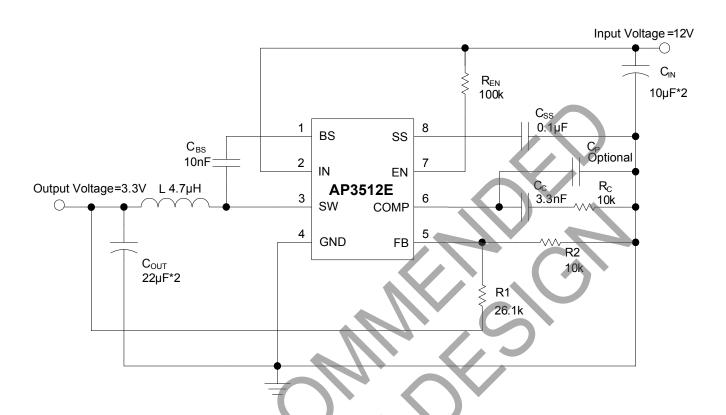
- Monitor
- TV
- STB
- Datacom

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Typical Applications Circuit

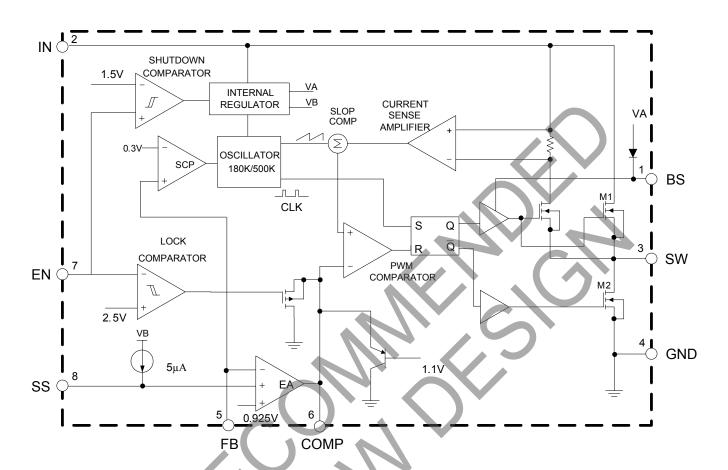


Pin Descriptions

Pin Number	Pin Name	Function
1	BS	Bootstrap pin. A bootstrap capacitor is connected between the BS pin and SW pin. The voltage across the bootstrap capacitor drives the internal high-side NMOS switch.
2	IN	Supply input pin. A capacitor should be connected between the IN pin and GND pin to keep the DC input voltage constant.
3	sw	Power switch output pin. This pin is connected to the inductor and bootstrap capacitor.
4	GND	Ground pin
5	FB	Feedback pin. This pin is connected to an external resistor divider to program the system output voltage. When the FB pin voltage exceeds 1.1V, the over voltage protection is triggered. When the FB pin voltage is below 0.3V, the oscillator frequency is lowered to realize short circuit protection.
6	COMP	Compensation pin. This pin is the output of the transconductance error amplifier and the input to the current comparator. This pin is used to compensate the control loop. Connect a series RC network from this pin to GND pin. In some cases, an additional capacitor from this pin to GND pin is required.
7	EN	Enable Input. EN is a digital input that turns the regulator on or off. Drive EN high to turn on the regulator, drive it low to turn off. Pull up with $100k\Omega$ resistor for automatic startup.
8	SS	Soft-start control input pin. SS controls the soft start period. Connect a capacitor from SS to GND to set the soft-start period. A 0.1µF capacitor sets the soft-start period to 15ms. To disable the soft-start feature, leave SS unconnected.
_	EP	Exposed pad. It should be connected to GND in PCB layout.



Functional Block Diagram





Absolute Maximum Ratings (Note 4)

Symbol	Parameter	Value	Unit
V _{IN}	IN Pin Voltage	-0.3 to 20	V
V _{EN}	EN Pin Voltage	-0.3 to V _{IN}	V
V _{SW}	SW Pin Voltage	21	V
V _{BS}	BS Pin Voltage	-0.3 to V _{SW} +6	V
V_{FB}	FB Pin Voltage	-0.3 to 6	V
V _{COMP}	COMP Pin Voltage	-0.3 to 6	V
V _{SS}	SS Pin Voltage	-0.3 to 6	V
TJ	Operating Junction Temperature	+150	°C
T _{STG}	Storage Temperature	-65 to +150	°C
T _{LEAD}	Lead Temperature (Soldering, 10s)	+260	°C
ӨЈА	Thermal Resistance (Junction to Ambient)	SO-8 105 SO-8EP 60	°C/W
V _{нвм}	ESD (Human Body Model)	2000	V
V _{MM}	ESD (Machine Model)	200	V

Note 4: Stresses greater than those listed under "Absolute Maximum Ratings" can cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods can affect device reliability.

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Unit
V _{IN}	Input Voltage	4.5	18	V
TA	Operating Ambient Temperature	-40	+85	°C



SUPPLY VOLTAGE (IN PIN) V _{IN} Input Voltage — 4.5 — 18 V Ig Quiescent Current V _{FB} =1V, V _{EN} =3.3V — 1.2 1.4 mA IsHON Shutdown Supply Current V _{EN} =0V — 0.1 1.0 µA UNDER VOLTAGE LOCKOUT V _{VIVO} Input UVLO Threshold V _N Rising 3.55 4.0 4.25 V EN Shutdown Threshold Voltage — 1.1 1.5 2 V EN Shutdown Threshold Voltage — 1.1 1.5 2 V — EN Shutdown Threshold Voltage — 1.1 1.5 2 V — EN Shutdown Threshold Voltage — 1.1 1.5 2 V — EN Shutdown Threshold Voltage — 1.1 1.5 2 V — EN Shutdown Threshold Voltage — 0.1 1.1 1.5 2 7 V <td< th=""><th>Symbol</th><th>Parameter</th><th>Conditions</th><th>Min</th><th>Тур</th><th>Max</th><th>Unit</th></td<>	Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Iq	SUPPLY VOLTA	AGE (IN PIN)						
Isi-IDN Shutdown Supply Current VEN=0V — 0.1 1.0 μA	V _{IN}	Input Voltage	_	4.5	_	18	V	
UNDER VOLTAGE LOCKOUT VUVLO Input UVLO Threshold Vn Rising 3.65 4.0 4.25 V ENShutdown Threshold Voltage — 1.1 1.5 2 V EN Shutdown Threshold Voltage — 1.1 1.5 2 V — EN Shutdown Threshold Voltage Hysteresis (Note 5) — — 3.50 — mV — EN Lockout Threshold Voltage — — 2.2 2.5 2.7 V — EN Lockout Hysteresis — — 2.10 — mV VOLTAGE REFERENCE (FB PIN) — — 2.10 — mV VFBO Feedback Voltage — 0.607 0.925 0.943 V VFBO Feedback Voltage Threshold — — 1.1 — V VFBOV Feedback Siliac Current VSMETALV — 1.0 — mC MOSTAGE Switch Current Limit — <td>IQ</td> <td>Quiescent Current</td> <td>V_{FB}=1V, V_{EN}=3.3V</td> <td>_</td> <td>1.2</td> <td>1.4</td> <td>mA</td>	IQ	Quiescent Current	V _{FB} =1V, V _{EN} =3.3V	_	1.2	1.4	mA	
Vuv.o.0 Input UVLO Threshold V _{IN} Rising 3.65 4.0 4.25 V ENABLE (EN PIN) — EN Shutdown Threshold Voltage — 1.1 1.5 2 V — EN Shutdown Threshold Voltage — 1.1 1.5 2 V — EN Lockout Threshold Voltage — 2.2 2.5 2.7 V — EN Lockout Threshold Voltage — 2.1 2 2.5 2.7 V — EN Lockout Hysteresis — — 2.10 — mV VOLTAGE REFERENCE (FB PIN) VFB Feedback Voltage — 0.907 0.925 0.943 V VFB Feedback Voltage — 0.907 0.925 0.943 V VFB Feedback Voltage Threshold — — 1.1 — V VFBOV Feedback Voltage — 0.907 0.925 0.943 V VFB	I _{SHDN}	Shutdown Supply Current	V _{EN} =0V	_	0.1	1.0	μA	
No.	UNDER VOLTA	GE LOCKOUT						
ENABLE (EN PIN)	V _{UVLO}	Input UVLO Threshold	V _{IN} Rising	3.65	4.0	4.25	V	
EN Shutdown Threshold Voltage	V _{HYS}	Input UVLO Hysteresis	_	. <	0.2	_	V	
EN Shutdown Threshold Voltage Hysteresis (Note 5)	ENABLE (EN PI	N)			-		I	
Companies Com	_	EN Shutdown Threshold Voltage	_	1.1	1.5	2	V	
— EN Lockout Hysteresis	_		-	_	350	_	mV	
VOLTAGE REFERENCE (FB PIN) VFB Feedback Voltage — 0,907 0,925 0,943 V VFBOV Feedback Over Voltage Threshold — — 1.1 — V IFB Feedback Bias Current VFB=1V —0.1 — 0.1 µA MOSFET RDSONH High-Side Switch On-resistance (Note 6) Isw=0.2A and 0.7A — 100 — mΩ CURRENT LIMIT ILEAKH High-Side Switch Leakage Current Vin=18V, VEN=0V, VSW=0V — 0.1 10 µA ILLIMIL High-Side Switch Current Limit — 4.3 5.6 — A ILLIMIL High-Side Switch Current Limit — 4.3 5.6 — A JUMB High-Side Switch Current Limit — 4.3 5.6 — A JUMB High-Side Switch Current Limit — 4.3 5.6 — A JUMB High-Side Switch Current Limit From drain	_	EN Lockout Threshold Voltage	-	2.2	2.5	2.7	V	
VFB Feedback Voltage — 0,907 0.925 0.943 V VFBOV Feedback Over Voltage Threshold — — 1.1 — V IFB Feedback Bias Current VFB=1V -0.1 — 0.1 µA MOSFET RDSONH High-Side Switch On-resistance (Note 6) Isw=0.2A and 0.7A — 100 — mΩ CURRENT LIMIT ILEAKH High-Side Switch Leakage Current Vin=18V, VEN=0V, VEN=0V, VEN=0V, VEN=0V, VEN=0V, VEN=0V — 0.1 10 µA ILIMIL High-Side Switch Current Limit — 4.3 5.6 — A ILIMIL Low-Side Switch Current Limit From drain to source — 50 — mA SWITCHING REGULATOR fosc1 Oscillator Frequency — 410 500 590 kHz DMAX Maximum Duty Cycle VFB=0.85V — 90 — % <td col<="" td=""><td>_</td><td>EN Lockout Hysteresis</td><td>$\forall I$</td><td></td><td>210</td><td>_</td><td>mV</td></td>	<td>_</td> <td>EN Lockout Hysteresis</td> <td>$\forall I$</td> <td></td> <td>210</td> <td>_</td> <td>mV</td>	_	EN Lockout Hysteresis	$\forall I$		210	_	mV
VFBOV Feedback Over Voltage Threshold — — 1.1 — V IFB Feedback Bias Current VFB=1V -0.1 — 0.1 µA MOSFET RDSONIL High-Side Switch On-resistance (Note 6) Isw=0.2A and -0.7A — 100 — mΩ CURRENT LIMIT ILEAKH High-Side Switch Leakage Current ViN=18V, VEN=0V, VSW=0V — 0.1 10 µA ILIMH High-Side Switch Current Limit — 4.3 5.6 — A ILIML Low-Side Switch Current Limit From drain to source — 50 — mA SWITCHING REGULATOR fosc1 Oscillator Frequency — 410 500 590 kHz fosc2 Short Circuit Oscillator Frequency — — 410 500 — % D _{MIN} Minimum Duty Cycle V _{FB} =0.85V — — 90 — % ERROR AMPLIFIER <td>VOLTAGE REFI</td> <td>ERENCE (FB PIN)</td> <td></td> <td></td> <td></td> <td></td> <td></td>	VOLTAGE REFI	ERENCE (FB PIN)						
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MOSFET RDSONH High-Side Switch On-resistance (Note 6) ¹Isw=0.2A and 0.7A — 100 — mΩ RDSONL Low-Side Switch On-resistance (Note 6) ¹Isw=-0.2A and -0.7A — 100 — mΩ CURRENT LIMIT ILEAKH High-Side Switch Leakage Current VIN=18V, VEN=0V, VSN=0V, VSN=0V, VSN=0V — 0.1 10 µA ILIMH High-Side Switch Current Limit — 4.3 5.6 — A ILIML Low-Side Switch Current Limit From drain to source — 50 — mA SWITCHING REGULATOR Frequency — 410 500 590 kHz fOSC1 Oscillator Frequency — 410 500 590 kHz DMAX Maximum Duty Cycle VFB=0.85V — 90 — % DMIN Minimum Duty Cycle VFB=1V — — 0 % ERROR AMPLIFIER Error Amplifier Voltage Gain (Note 5) —	V_{FBOV}	Feedback Over Voltage Threshold	- \	_	1.1	_	V	
RDSONH	I _{FB}	Feedback Bias Current	V _{FB} =1V	-0.1	_	0.1	μA	
RDSONL Low-Side Switch On-resistance (Note 6) J _{SW} =-0.2A and -0.7A — 100 — mΩ CURRENT LIMIT ILEAKH High-Side Switch Leakage Current V _{IN} =18V, V _{EN} =0V, V _{SW} =0V, — 0.1 10 μA ILIMH High-Side Switch Current Limit — 4.3 5.6 — A ILIML Low-Side Switch Current Limit From drain to source — 50 — mA SWITCHING REGULATOR fosc1 Oscillator Frequency — 410 500 590 kHz fosc2 Short Circuit Oscillator Frequency — — 180 — kHz D _{MAX} Maximum Duty Cycle V _{FB} =0.85V — 90 — % ERROR AMPLIFIER A _{EA} Error Amplifier Voltage Gain (Note 5) — — 400 — V/V	MOSFET							
CURRENT LIMIT I _{LEAKH} High-Side Switch Leakage Current V _{IN} =18V, V _{EN} =0V, V _{SW} =0V — 0.1 10 μA I _{LIMH} High-Side Switch Current Limit — 4.3 5.6 — A I _{LIML} Low-Side Switch Current Limit From drain to source — 50 — mA SWITCHING REGULATOR f _{OSC1} Oscillator Frequency — 410 500 590 kHz f _{OSC2} Short Circuit Oscillator Frequency — — 180 — kHz D _{MAX} Maximum Duty Cycle V _{FB} =0.85V — 90 — % D _{MIN} Minimum Duty Cycle V _{FB} =1V — — 0 % ERROR AMPLIFIER A _{EA} Error Amplifier Voltage Gain (Note 5) — — 400 — V/V	R _{DSONH}	High-Side Switch On-resistance (Note 6)	I _{SW} =0.2A and 0.7A	_	100	_	mΩ	
ILEAKH	R _{DSONL}	Low-Side Switch On-resistance (Note 6)	I _{SW} =-0.2A and -0.7A	_	100	_	mΩ	
ILEAKH High-Side Switch Leakage Current V _{SW} =0V — 0.1 10 μA	CURRENT LIMI		•					
I _{LIML} Low-Side Switch Current Limit From drain to source — 50 — mA SWITCHING REGULATOR f _{OSC1} Oscillator Frequency — 410 500 590 kHz f _{OSC2} Short Circuit Oscillator Frequency — — 180 — kHz D _{MAX} Maximum Duty Cycle V _{FB} =0.85V — 90 — % D _{MIN} Minimum Duty Cycle V _{FB} =1V — — 0 % ERROR AMPLIFIER A _{EA} Error Amplifier Voltage Gain (Note 5) — — 400 — V/V	ILEAKH	High-Side Switch Leakage Current		_	0.1	10	μΑ	
SWITCHING REGULATOR f _{OSC1} Oscillator Frequency — 410 500 590 kHz f _{OSC2} Short Circuit Oscillator Frequency — — 180 — kHz D _{MAX} Maximum Duty Cycle V _{FB} =0.85V — 90 — % D _{MIN} Minimum Duty Cycle V _{FB} =1V — — 0 % ERROR AMPLIFIER A _{EA} Error Amplifier Voltage Gain (Note 5) — — 400 — V/V	Іцімн	High-Side Switch Current Limit	_	4.3	5.6	_	Α	
f _{OSC1} Oscillator Frequency — 410 500 590 kHz f _{OSC2} Short Circuit Oscillator Frequency — — 180 — kHz D _{MAX} Maximum Duty Cycle V _{FB} =0.85V — 90 — % D _{MIN} Minimum Duty Cycle V _{FB} =1V — — 0 % ERROR AMPLIFIER A _{EA} Error Amplifier Voltage Gain (Note 5) — — 400 — V/V	I _{LIML}	Low-Side Switch Current Limit	From drain to source	_	50	_	mA	
f _{OSC2} Short Circuit Oscillator Frequency — — 180 — kHz D _{MAX} Maximum Duty Cycle V _{FB} =0.85V — 90 — % D _{MIN} Minimum Duty Cycle V _{FB} =1V — — 0 % ERROR AMPLIFIER A _{EA} Error Amplifier Voltage Gain (Note 5) — — 400 — V/V	SWITCHING RE	GULATOR						
D _{MAX} Maximum Duty Cycle V _{FB} =0.85V — 90 — % D _{MIN} Minimum Duty Cycle V _{FB} =1V — — 0 % ERROR AMPLIFIER A _{EA} Error Amplifier Voltage Gain (Note 5) — — 400 — V/V	f _{OSC1}	Oscillator Frequency	_	410	500	590	kHz	
D _{MIN} Minimum Duty Cycle V _{FB} =1V — — 0 % ERROR AMPLIFIER A _{EA} Error Amplifier Voltage Gain (Note 5) — — 400 — V/V	fosc2	Short Circuit Oscillator Frequency	_	_	180	_	kHz	
ERROR AMPLIFIER A _{EA} Error Amplifier Voltage Gain (Note 5) — — 400 — V/V	D_{MAX}	Maximum Duty Cycle	V _{FB} =0.85V	_	90	_	%	
A _{EA} Error Amplifier Voltage Gain (Note 5) — — 400 — V/V	D _{MIN}	Minimum Duty Cycle	V _{FB} =1V	_		0	%	
	ERROR AMPLIF	FIER						
G _{EA} Error Amplifier Transconductance — — 800 — μΑ/V	A _{EA}	Error Amplifier Voltage Gain (Note 5)	_	_	400	_	V/V	
	GEA	Error Amplifier Transconductance	_	_	800	_	μA/V	
G _{CS} COMP to Current Sense Transconductance — 5.2 — A/V	Gcs	COMP to Current Sense Transconductance	_	_	5.2	_	A/V	



Electrical Characteristics (continued) (V_{IN}=V_{EN}=12V, V_{OUT}=3.3V, T_A=+25°C, unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
THERMAL SHUTDOWN						
T _{OTSD}	Thermal Shutdown (Note 5)	_	_	+160	_	°C
T _{HYS}	Thermal Shutdown Hysteresis (Note 5)	_	_	+30	1	°C
SOFT START (SS PIN)						
tss	Soft-Start Time (Note 5)	C _{SS} =0.1µF	_	15	_	ms
_	Soft-Start Current	_	70	5	_	μΑ

Notes: 5. Not tested, guaranteed by design.

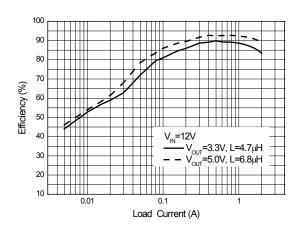
6.
$$R_{DS(ON)} = \frac{V_{SW1} - V_{SW2}}{I_{SW1} - I_{SW2}}$$



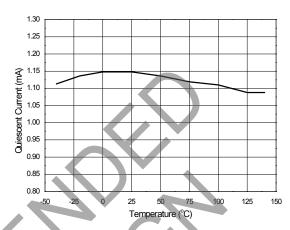


Performance Characteristics (V_{IN}=12V, V_{OUT}=3.3V, L=4.7µH, T_A=+25°C, unless otherwise noted.)

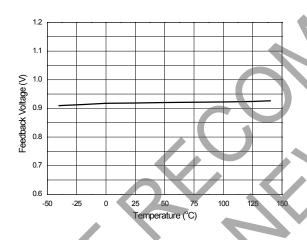
Efficiency vs. Load Current



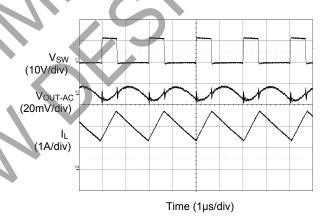
Quiescent Current vs. Temperature



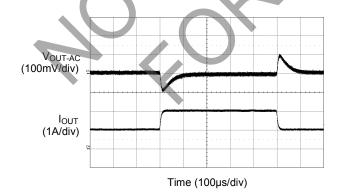
Feedback Voltage vs. Temperature



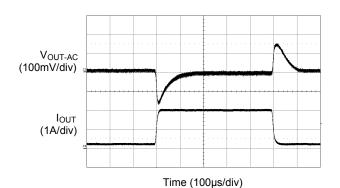
Output Ripple (I_{OUT}=2A)



Load Transient Response (I_{OUT}=1A to 2A)



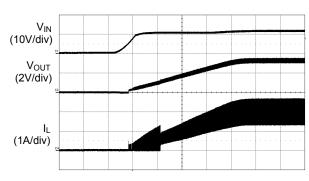
Load Transient Response (I_{OUT}=0.2A to 2A)





Performance Characteristics (continued) (V_{IN}=12V, V_{OUT}=3.3V, L=4.7µH, T_A=+25°C, unless otherwise noted.)

Power On from V_{IN} (I_{OUT}=2A)



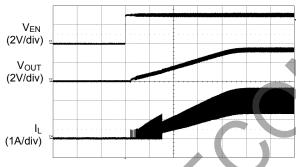
Time (3.20ms/div)

Power Off from V_{IN} (I_{OUT}=2A)



Time (3.20ms/div)

Power On from EN (I_{OUT}=2A)



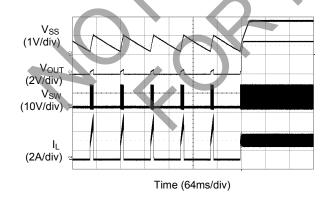
Time (3.20ms/div)

Power Off from EN (I_{OUT}=2A)

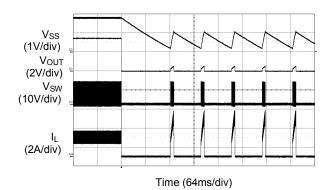


Time (3.20ms/div)

Short Circuit Protection (I_{OUT}=2A)

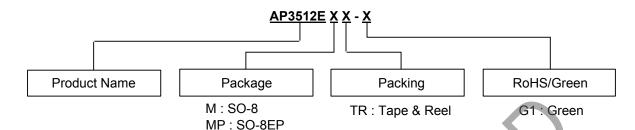


Short Circuit Protection Recovery (I_{OUT}=2A)





Ordering Information



Package (Note 8)	Temperature Range	Part Number	Packing	Status (Note 7)
SO-8	-40 to +85°C	AP3512EMTR-G1	4000/Tape & Reel	In production
SO-8EP	-40 to +85°C	AP3512EMPTR-G1	4000/Tape & Reel	In production

Notes: 7. All Tube versions are End of Life with replacement in Tape & Reel versions.

8. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information

(1) SO-8



(2) SO-8EP

(Top View)

First and Second Lines: Logo and Marking ID

Third Line: Date Code

Y: Year

WW: Work Week of Molding

A: Assembly Site Code XX: 7th and 8th Digits of Batch Number

First and Second Lines: Logo and Marking ID

Third Line: Date Code

Y: Year

WW: Work Week of Molding

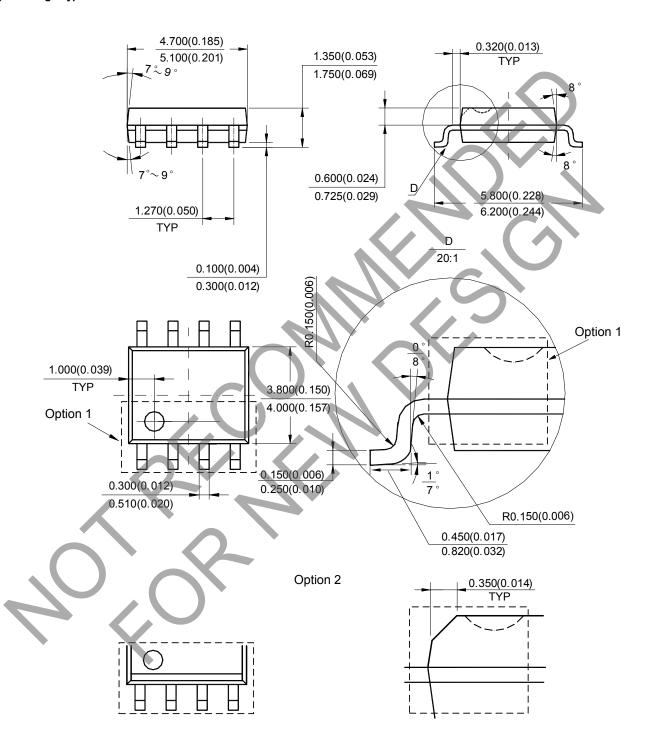
A: Assembly Site Code XX: 7th and 8th Digits of Batch Number



Package Outline Dimensions (All dimensions in mm(inch).)

Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) Package Type: SO-8



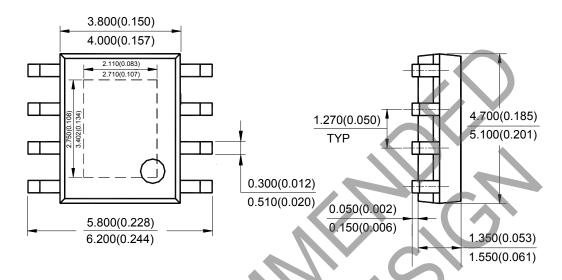
Note: Eject hole, oriented hole and mold mark is optional.

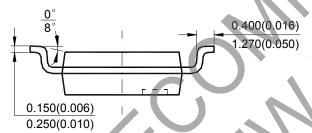


Package Outline Dimensions (continued. All dimensions in mm (inch).)

Please see http://www.diodes.com/package-outlines.html for the latest version.

(2) Package Type: SO-8EP





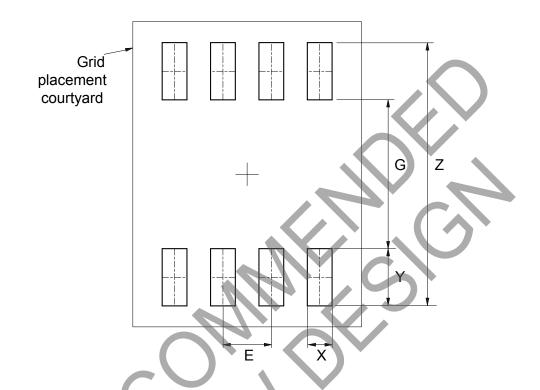
Note: Eject hole, oriented hole and mold mark is optional.



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) Package Type: SO-8



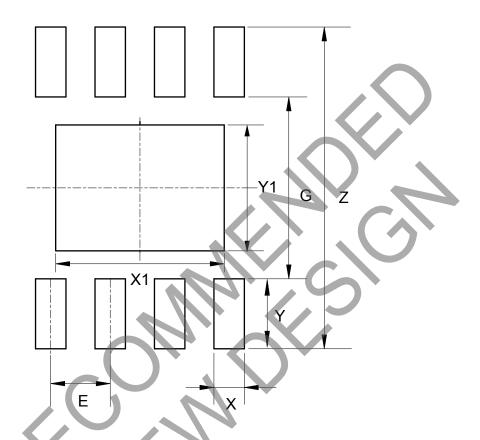
Dimensions	Z	G	X	Y	E
	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)
Value	6.900/0.272	3.900/0.154	0.650/0.026	1.500/0.059	1.270/0.050



Suggested Pad Layout (continued)

Please see http://www.diodes.com/package-outlines.html for the latest version.

(2) Package Type: SO-8EP



Dimensions	Z (mm)/(inch)	G (mm)/(inch)	(mm)/(inch)	Y (mm)/(inch)	X1 (mm)/(inch)	Y1 (mm)/(inch)	E (mm)/(inch)
Value	6.900/0.272	3.900/0.154	0.650/0.026	1.500/0.059	3.600/0.142	2.700/0.106	1.270/0.050



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